



STC12IE90HV

Emitter Switched Bipolar Transistor
ESBT® 900 V - 12 A - 0.083 Ω

Preliminary Data

General features

$V_{CS(ON)}$	I_C	$R_{CS(ON)}$
1V	12A	0.083 Ω

- High voltage / high current Cascode configuration
- Low equivalent on resistance
- Very fast-switch up to 150 kHz
- Squared RBSOA up to 900V
- Very low C_{iss} driven by $R_G = 47\Omega$
- Very low turn-off cross over time

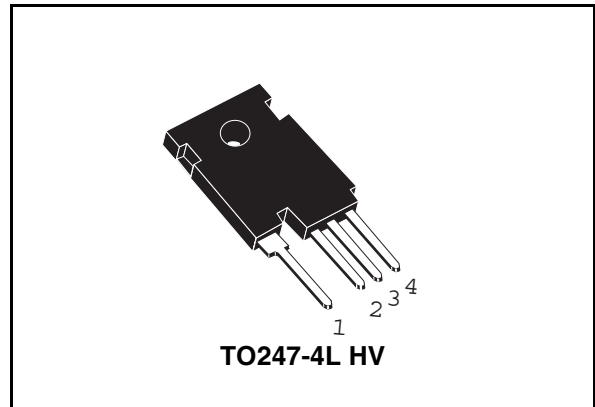
Applications

- Aux Smpls For Three Phase Mains

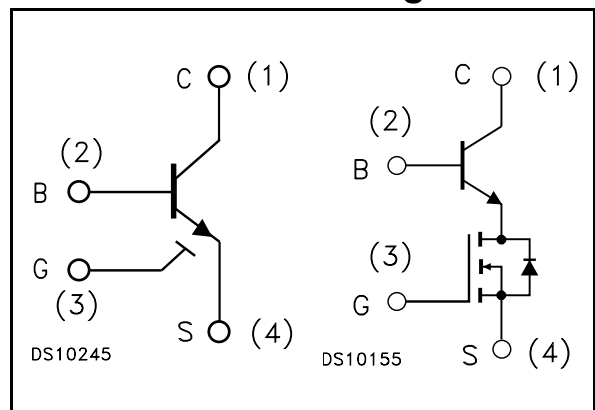
Description

The STC12IE90HV is manufactured in Monolithic ESBT Technology, aimed to provide best performances in high frequency / high voltage applications.

It is designed for use in Gate Driven based topologies.



Internal schematic diagrams



Order codes

Part Number	Marking	Package	Packaging
STC12IE90HV	C12IE90HV	TO247-4L HV	Tube

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1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
$V_{CS(SS)}$	Collector-source voltage ($V_{BS} = V_{GS} = 0\text{ V}$)	900	V
$V_{BS(OS)}$	Base-source voltage ($I_C = 0, V_{GS} = 0\text{ V}$)	30	V
$V_{SB(OS)}$	Source-base voltage ($I_C = 0, V_{GS} = 0\text{ V}$)	17	V
V_{GS}	Gate-source voltage	± 17	V
I_C	Collector current	12	A
I_{CM}	Collector peak current ($t_P < 5\text{ms}$)	36	A
I_B	Base current	6	A
I_{BM}	Base peak current ($t_P < 5\text{ms}$)	10	A
P_{tot}	Total dissipation at $T_c = 25^\circ\text{C}$	208	W
T_{stg}	Storage temperature	-40 to 150	$^\circ\text{C}$
T_J	Max. operating junction temperature	150	$^\circ\text{C}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.6	$^\circ\text{C/W}$

2 Electrical characteristics

($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise specified)

Table 3. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{\text{CS(SS)}}$	Collector-source current ($V_{\text{BS}} = V_{\text{GS}} = 0$)	$V_{\text{CE}} = 900\text{V}$			100	μA
$I_{\text{BS(OS)}}$	Base-source current ($I_{\text{C}} = 0, V_{\text{GS}} = 0$)	$V_{\text{BS(OS)}} = 30\text{V}$			10	μA
$I_{\text{SB(OS)}}$	Source-base current ($I_{\text{C}} = 0, V_{\text{GS}} = 0$)	$V_{\text{SB(OS)}} = 17\text{V}$			100	μA
$I_{\text{GS(OS)}}$	Gate-source leakage	$V_{\text{GS}} = \pm 17\text{V}$			100	nA
$V_{\text{CS(ON)}}$	Collector-source ON voltage	$V_{\text{GS}} = 10\text{V} \quad I_{\text{C}} = 12\text{A} \quad I_{\text{B}} = 2.4\text{A}$ $V_{\text{GS}} = 10\text{V} \quad I_{\text{C}} = 6\text{A} \quad I_{\text{B}} = 0.6\text{A}$		1 0.6		V V
h_{FE}	DC current gain	$V_{\text{GS}} = 10\text{V} \quad I_{\text{C}} = 12\text{A} \quad V_{\text{CS}} = 1\text{V}$ $V_{\text{GS}} = 10\text{V} \quad I_{\text{C}} = 6\text{A} \quad V_{\text{CS}} = 1\text{V}$		5 15		
$V_{\text{BS(ON)}}$	Base Source ON voltage	$V_{\text{GS}} = 10\text{V} \quad I_{\text{C}} = 12\text{A} \quad I_{\text{B}} = 2.4\text{A}$ $V_{\text{GS}} = 10\text{V} \quad I_{\text{C}} = 6\text{A} \quad I_{\text{B}} = 0.6\text{A}$		1.5 1.2		V V
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{BS}} = V_{\text{GS}} \quad I_{\text{B}} = 250\mu\text{A}$	2	3	4	V
C_{iss}	Input capacitance	$V_{\text{CS}} = 25\text{V} \quad f = 1\text{MHz}$ $V_{\text{GS}} = 0\text{V}$		520		pF
$Q_{\text{GS(tot)}}$	Gate-source Charge	$V_{\text{CS}} = 25\text{V} \quad V_{\text{GS}} = 10\text{V}$ $V_{\text{CB}} = 0\text{V} \quad I_{\text{C}} = 4\text{A}$		21.3		nC
t_{s} t_{f}	INDUCTIVE LOAD Storage time Fall time	$V_{\text{GS}} = 10\text{V} \quad R_{\text{G}} = 47\Omega$ $V_{\text{Clamp}} = 720\text{V} \quad t_{\text{p}} = 4\mu\text{s}$ $I_{\text{C}} = 6\text{A} \quad I_{\text{B}} = 1.2\text{A}$		610 10		ns ns
t_{s} t_{f}	INDUCTIVE LOAD Storage time Fall time	$V_{\text{GS}} = 10\text{V} \quad R_{\text{G}} = 47\Omega$ $V_{\text{Clamp}} = 720\text{V} \quad t_{\text{p}} = 4\mu\text{s}$ $I_{\text{C}} = 6\text{A} \quad I_{\text{B}} = 0.6\text{A}$		360 10		ns ns
V_{CSW}	Maximum collector-source voltage switched without snubber	$R_{\text{G}} = 47\Omega$ $I_{\text{C}} = 12\text{A} \quad h_{\text{FE}} = 5$	900			V

Table 3. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CS(dyn)}$	Collector-source dynamic voltage (500ns)	$V_{CC}=V_{Clamp}=400V$ $V_{GS}=10V$ $I_C=6A$ $I_B=1.2A$ $t_{peak}=500ns$ $R_G=47\Omega$ $I_{Bpeak}=6A(I_C)$		3.37		V
$V_{CS(dyn)}$	Collector-source dynamic voltage (1μs)	$V_{CC}=V_{Clamp}=400V$ $V_{GS}=10V$ $I_C=6A$ $I_B=1.2A$ $t_{peak}=500ns$ $R_G=47\Omega$ $I_{Bpeak}=6A(I_C)$		1.75		V

2.1 Electrical characteristics (curves)

Figure 1. DC current gain

Figure 2. Collector-source On voltage

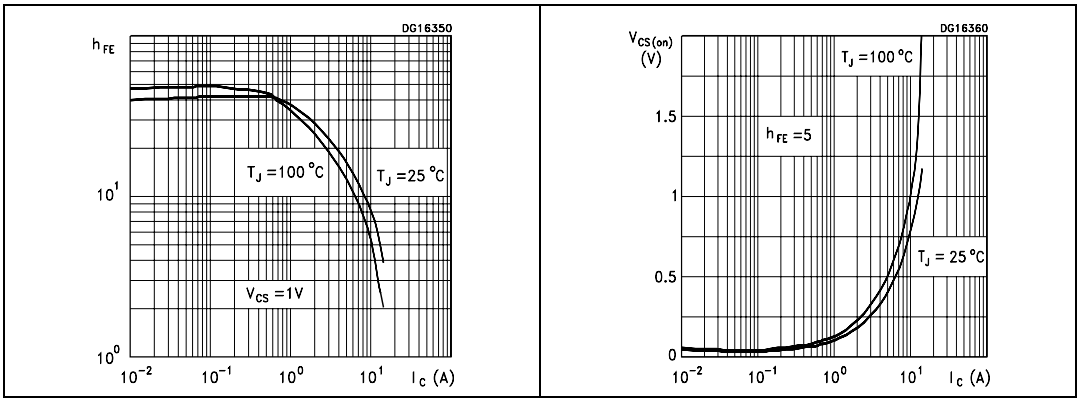


Figure 3. Collector-source On voltage

Figure 4. Base-source On voltage

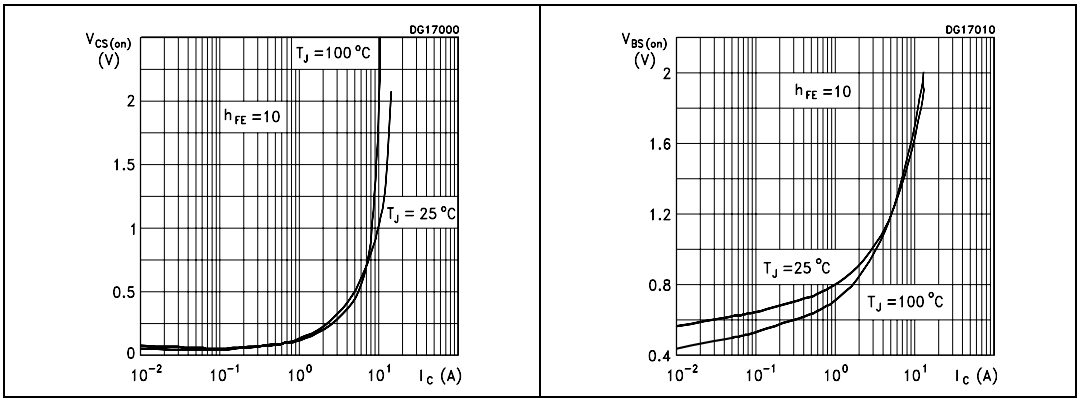


Figure 5. Reverse biased SOA

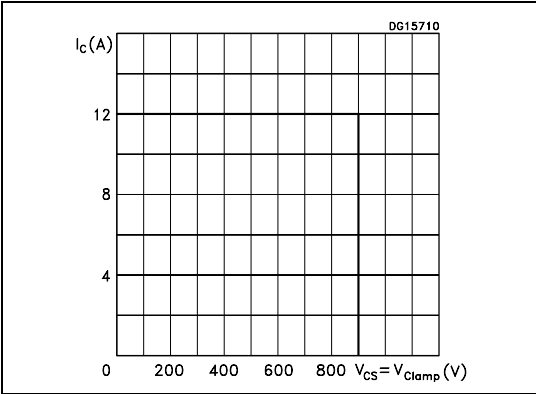


Figure 6. Dynamic collector-emitter voltage

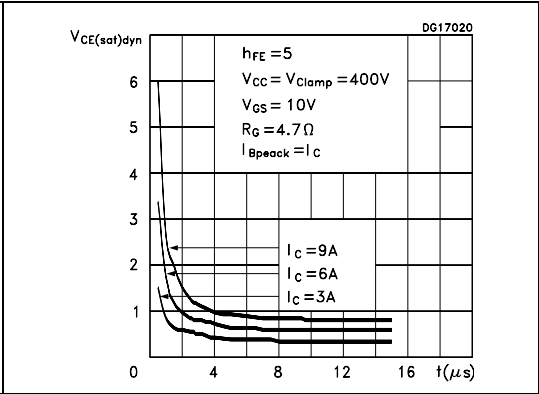


Figure 7. Inductive load switching time

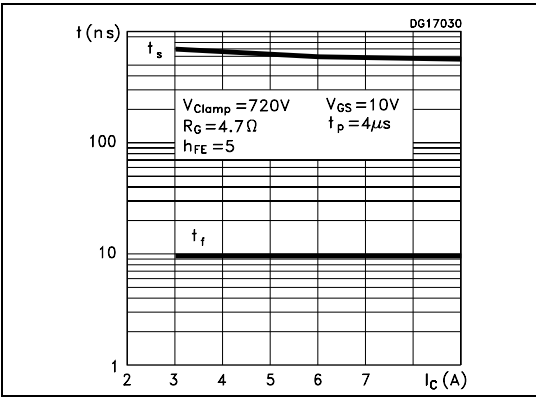
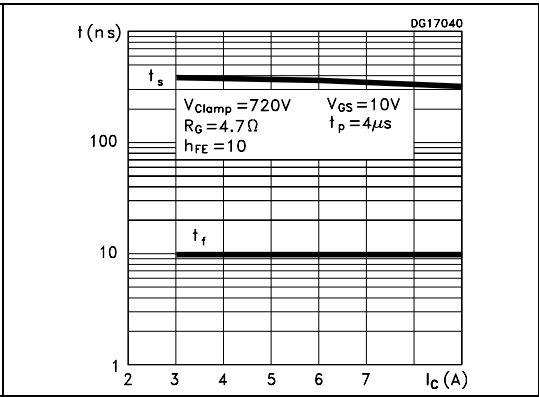


Figure 8. Inductive load switching time



2.2 Test circuits

Figure 9. Static $V_{CS(ON)}$ test circuits

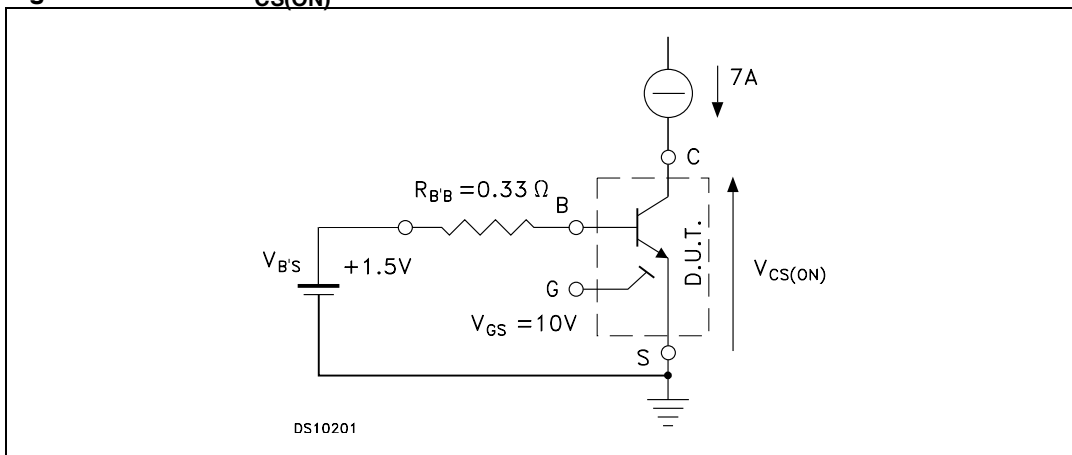
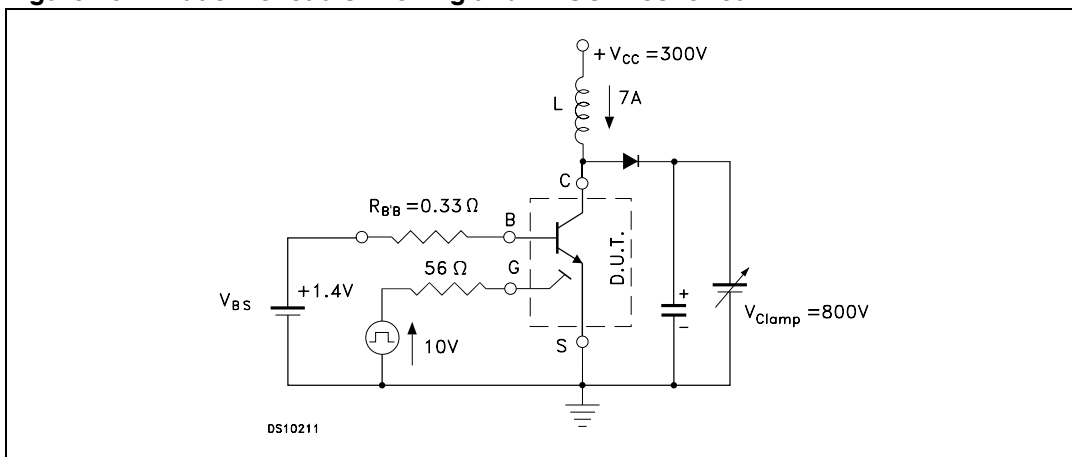


Figure 10. Inductive load switching and RBSOA test circuit

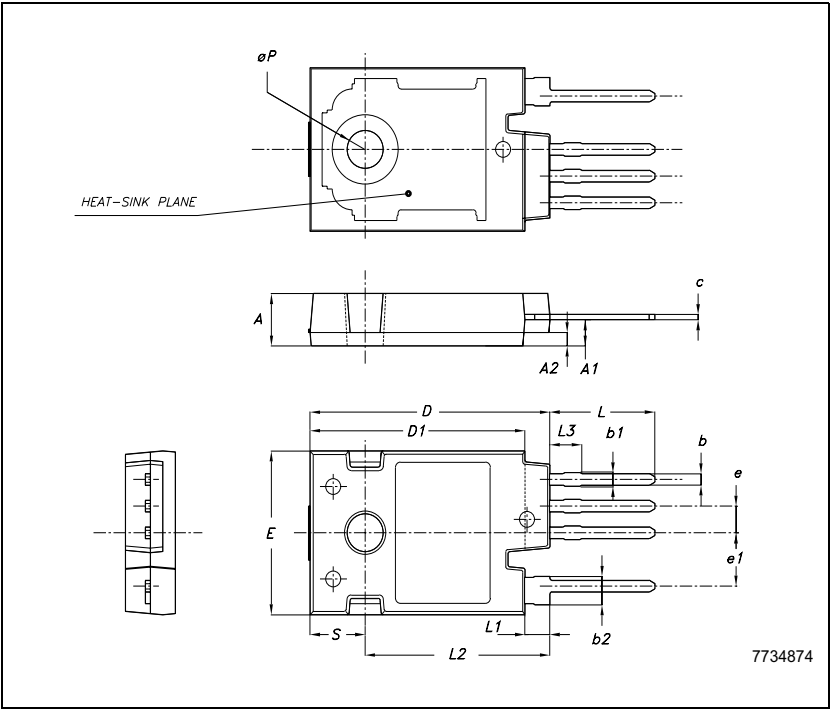


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO247-4L HV MECHANICAL DATA

DIM.	mm.		
	MIN.	TYP	MAX.
A	4.85		5.15
A1	2.20	2.50	2.60
A2		1.27	
b	0.95	1.10	1.30
b2	2.50		2.90
c	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15.75
e	2.54		
e1	5.08		
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
øP	3.55		3.65
S		5.50	



4 Revision history

Table 4. Revision history

Date	Revision	Changes
16-Jan-2007	1	Initial release.

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